FORM: PTO-1449 (REV: 7-80)		U.S. DEPARTMENT OF COMMERCE			Atty Docket No:	Serial No:	
		PATENT AND TRADEMARK OFFICE		2000-0116.01/US	10/78	1,535	
Applicant:							'
INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Kelly T. Hurley		
				Filing Date:	Group:	\sim	
(37 CFR 1.98(b))		(use several sheets if necessary)		February 26, 2004	28	322	
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		ъ.		U.S. PATENT DOCUMEN	TS		
Examiner Initial		Document Number	D-4-	X	A 1		
JMJ	AA	6,271,087	Date 08/07/2001	Name Kinoshita et al.	Class	Subclass	
J.11.1	AB	6,188,115	02/13/2001	Kamitani	438	258	
	AC	6,080,624	06/27/2000	Kamiya et al.	257	412	
	AD	5,994,733	11/30/1999	Nishioka et al.	438	257	
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	AH		 			 	
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		•	FC	DREIGN PATENT DOCUM	ENTS		
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Initial		Number	Date	Country	Class	Subclass	Yes No
Initial	AL		Date	Country	Class	Subclass	
Initial	AM		Date	Country	Class	Subclass	
Initial	AM AN		Date	Country	Class	Subclass	
Initial	AM AN AO		Date	Country	Class	Subclass	
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Initial	AM AN AO		Date	Country	Class	Subclass	
	AM AN AO AP						
Initial	AM AN AO AP	Number	OTF	HER ART (including author, t	itle, date, pertinent pages,	etc.)	Yes No
	AM AN AO AP AQ	Number "A	OTF 130-mm2, 256	IER ART (including author, to 5-Mbit NAND Flash with Shall	itle, date, pertinent pages,	etc.)	Yes No
Initial	AM AN AO AP	Number "A	OTF 130-mm2, 256	HER ART (including author, t	itle, date, pertinent pages,	etc.)	Yes No
	AM AN AO AP AQ	Number "A	OTF 130-mm2, 256 al., IEEE Journ	HER ART (including author, to S-Mbit NAND Flash with Shall al of Solid-State Circuits, Vol.	itle, date, pertinent pages, low Trench Isolation Tech 34, No. 11, November 19	etc.) nology", Kenicl	Yes No
Initial	AM AN AO AP AQ	Number "A et	OTF 130-mm2, 256 al., IEEE Journ lovel 0.44µm2	HER ART (including author, to 5-Mbit NAND Flash with Shall al of Solid-State Circuits, Vol. Ti-Salicide STI Cell Technology	itle, date, pertinent pages, low Trench Isolation Tech 34, No. 11, November 199	etc.) nology", Kenich	Yes No
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Initial JMJ LMJ Examiner:	AM AN AO AP AQ AR AS	Number "A et	OTF 130-mm2, 256 al., IEEE Journ Jovel 0.44µm2 rformance Emb	HER ART (including author, to 5-Mbit NAND Flash with Shall al of Solid-State Circuits, Vol. Ti-Salicide STI Cell Technology	itle, date, pertinent pages, low Trench Isolation Tech 34, No. 11, November 19 gy for High Density NOR abe et al.,IEDM 98, pp. 97	etc.) nology", Kenich	Yes No

EXAMINER:

Initial if reference considered, whether or not citation is in conformance with MPEP §609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication with applicant.